Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Withdrawn) A wafer polishing process comprising:

polishing a surface of a wafer in the presence of an oxidizer-free medium; and, subsequently,

polishing the surface of the wafer in the presence of an oxidizing medium.

2. (Withdrawn) The wafer polishing process of claim 1, wherein said oxidizer-free medium comprises an oxidizer-free slurry, and said oxidizing medium comprises an oxidizing slurry.

3. (Withdrawn) The wafer polishing process of claim 1, wherein said oxidizer-free medium comprises an oxidizer-free fluid, and said oxidizing medium comprises an oxidizing fluid.

4. (Withdrawn) The wafer polishing process of claim 1, wherein said polishing in the presence of an oxidizer-free medium and said polishing in the presence of an oxidizing medium both occur at a first polishing station.

5. (Withdrawn) The wafer polishing process of claim 4, further comprising,

transferring said wafer from said first polishing station to a second polishing station; and

polishing said surface of said wafer in the presence of an oxidizing medium at said second polishing station.

6. (Withdrawn) The wafer polishing process of claim 1, wherein said polishing in the presence of an oxidizer-free medium occurs at a first polishing station and said polishing in the presence of an oxidizing medium occurs at a second polishing station.

7. (Withdrawn) The wafer polishing process of claim 1, wherein said polishing in the presence of an oxidizer-free medium and said polishing in the presence of an oxidizing medium both comprise linear chemical-mechanical polishing.

8. (Withdrawn) The wafer polishing process of claim 1, wherein said surface comprises a copper-containing component.

9. (Withdrawn) The process of claim 8, wherein said oxidizing medium comprises at least one oxidizer capable of oxidizing at least a portion of said copper-containing component.

10. (Withdrawn) A wafer polishing process comprising:

supplying an oxidizer-free medium to a polishing portion of a polishing station;

polishing a surface of a wafer in the presence of said oxidizer-free medium at said polishing station;

discontinuing the supply of said oxidizer-free medium to the polishing portion;

supplying an oxidizing medium to the polishing portion; and

polishing the surface of the wafer in the presence of said oxidizing medium at said polishing portion.

11. (Withdrawn) The wafer polishing process of claim 10, wherein said surface comprises a copper-containing component.

12. (Withdrawn) The wafer polishing process of claim 10, wherein said oxidizer-free medium comprises an oxidizer-free slurry, and said oxidizing medium comprises an oxidizing slurry.

13. (Withdrawn) The wafer polishing process of claim 10, wherein said oxidizer-free medium comprises an oxidizer-free fluid, and said oxidizing medium comprises an oxidizing fluid.

14. (Withdrawn) A wafer polishing process comprising:

chemically-mechanically polishing a copper-containing surface of a wafer in the presence of an oxidizer-free slurry at a first polishing station;

transferring the wafer from said first polishing station to a second polishing station; and

chemically-mechanically polishing the copper-containing surface of the wafer in the presence of an oxidizing slurry at said second polishing station.

15. (Currently amended) A wafer polishing system comprising:

a first chemical-mechanical polishing station having a polishing portion;

a source of an oxidizer-free medium ~~in communication with said polishing portion~~; ~~and~~

a source of an oxidizing medium ~~in communication with said polishing portion~~; and

a delivery system adapted for delivering said oxidizer-free medium to a wafer in said polishing station prior to delivering said oxidizing medium to said wafer in said polishing station;

wherein said source of an oxidizer-free medium and said source of an oxidizing medium are maintained separately ~~and wherein said source of an oxidizer-free medium is utilized by said polishing station prior to said source of an oxidizing medium to polish a surface of a wafer~~.

16. (Original) The wafer polishing system of claim 15, further comprising:

a second polishing station; and

a transfer mechanism adapted to move said wafer from said first polishing station to said second polishing station.

17. (Currently amended) A wafer polishing system comprising:

a first polishing station adapted to polish a surface of a wafer in the presence of an oxidizer-free medium;

a source of an oxidizer-free medium ~~in communication with said first polishing station~~;

a second polishing station adapted to polish said surface of said wafer in the presence of an oxidizing medium;

a source of an oxidizing medium ~~in communication with said second polishing station; and~~

a transfer mechanism adapted to move a wafer to and from said first polishing station ~~to~~ and said second polishing station; and

a delivery system,

wherein said delivery system is adapted to deliver said oxidizer-free medium to said first polishing station in order to polish said wafer;

wherein said transfer mechanism is adapted to move said wafer to said second polishing station; and

wherein said delivery system is adapted to deliver said oxidizing medium to said second station in order to polish said wafer.

18. (Currently amended) The wafer polishing system of claim 17, wherein said delivery system is adapted to deliver said ~~source of~~ oxidizing solution ~~is also in communication with~~ to said first polishing station.

19. (Currently amended) The wafer polishing system of claim 17, further comprising:

a second source of an oxidizing medium ~~in communication with said first polishing station~~; and

wherein said delivery system is adapted to deliver said second source of oxidizing medium to said first polishing station.

20. (Original) The wafer polishing station of claim 17, wherein said oxidizer-free medium comprises an oxidizer-free slurry, and said oxidizing medium comprises an oxidizing slurry.

21. (Currently amended) A wafer polishing system comprising:

a plurality of polishing stations;

a delivery system adapted for supplying an oxidizer-free medium to at least one of said polishing stations to polish a surface of a wafer and for supplying an oxidizing medium to at least one of said polishing stations to polish said wafer surface; and

~~a delivery system for supplying an oxidizing medium to at least one of said polishing stations to polish said wafer surface;~~

a transfer mechanism adapted to move said wafer among said plurality of polishing stations;

wherein said delivery system and said transfer mechanism act cooperatively to supply oxidizer-free medium ~~polishes the~~ onto a specific wafer surface prior to supplying ~~the~~ oxidizing medium onto said specific wafer surface.

22. (Previously added) The wafer polishing system of claim 21, wherein said oxidizer-free medium and said oxidizing medium are delivered to the same polishing station.

23. (Previously added) The wafer polishing system of claim 21, wherein said oxidizer-free medium and said oxidizing medium are delivered to different polishing stations.

24. (New) The wafer polishing system of claim 15, wherein said delivery system discontinues delivering said oxidizer-free medium to said wafer in said polishing station and subsequently begins delivering said oxidizing medium to said wafer in said polishing station.

25. (New) The wafer polishing system of claim 17, wherein said transfer mechanism moves said wafer from said first polishing station to said second polishing station.